

Fabrizio Roccaforte received the M.Sc. Degree in Physics from the University of Catania (Italy) in 1996, and the PhD from the University of Göttingen (Germany) in 1999. After being visiting scientist at the University of Göttingen, and scientific consultant at STMicroelectronics (Italy), he joined CNR-IMM in Catania as a Researcher in 2001, and he became Senior Researcher in 2007 and Research Director in 2020.

His research interests are mainly focused on wide band gap (WBG) semiconductors, (e.g., SiC, GaN, Ga₂O₃,...) materials and devices processing for power electronics devices. In particular, he has a recognized experience on metal/semiconductor and dielectric/semiconductor interfaces on WBG semiconductors.

He is co-author of about 350 papers in international journals and proceedings, several review articles, 8 book chapters, 5 patents, and he has given several invited talks and lectures at international conferences. He has been the chairperson of three international conferences, member of the Steering Committee of ECSCRM and EXMATEC, and responsible of CNR-IMM research unit in several European and National projects.